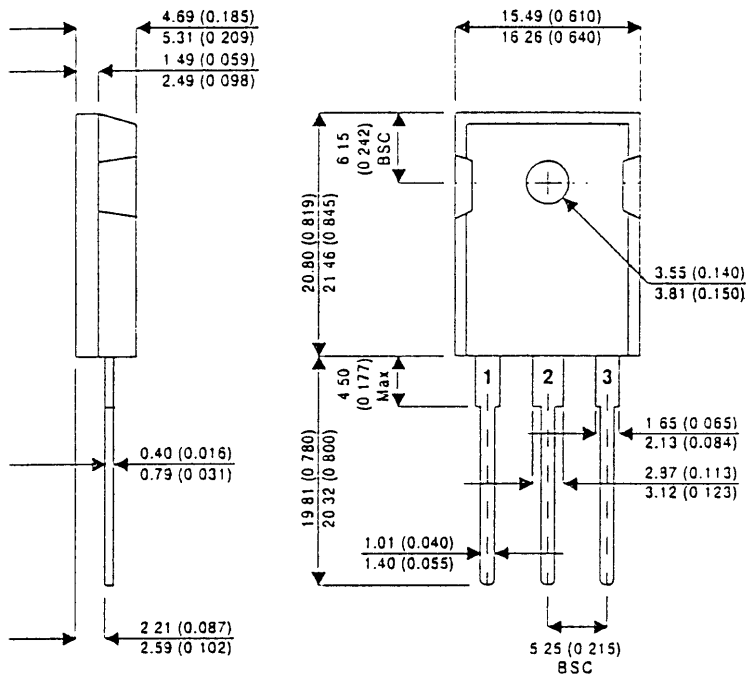


MECHANICAL DATA

Dimensions in mm (inches)



TO-247

Pin 1 – Gate

Pin 2 – Source

Pin 3 – Drain

N-CHANNEL POWER MOSFET

POWER MOSFETS FOR AUDIO APPLICATIONS

FEATURES

- HIGH SPEED SWITCHING
- N-CHANNEL POWER MOSFET
- SEMEFAB DESIGNED AND DIFFUSED
- HIGH VOLTAGE (160V & 200V)
- HIGH ENERGY RATING
- ENHANCEMENT MODE
- INTEGRAL PROTECTION DIODE
- P-CHANNEL ALSO AVAILABLE AS BUZ905P & BUZ906P

ABSOLUTE MAXIMUM RATINGS

($T_{case} = 25^{\circ}\text{C}$ unless otherwise stated)

		BUZ900P	BUZ901P
V_{DSX}	Drain – Source Voltage	160V	200V
V_{GSS}	Gate – Source Voltage	$\pm 14\text{V}$	
I_D	Continuous Drain Current	8A	
$I_{D(PK)}$	Body Drain Diode	8A	
P_D	Total Power Dissipation @ $T_{case} = 25^{\circ}\text{C}$	125W	
T_{stg}	Storage Temperature Range	-55 to 150°C	
T_j	Maximum Operating Junction Temperature	150°C	
$R_{\theta JC}$	Thermal Resistance Junction – Case	1.0°C/W	

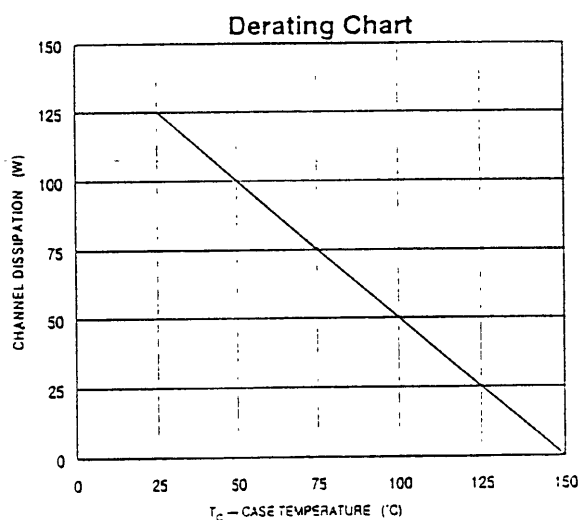
STATIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
BV_{DSX} Drain – Source Breakdown Voltage	$V_{GS} = -10V$ $I_D = 10mA$	BUZ900P	160			V
		BUZ901P	200			
BV_{GSS} Gate – Source Breakdown Voltage	$V_{DS} = 0$	$I_G = \pm 100\mu A$	± 14			V
$V_{GS(OFF)}$ Gate – Source Cut-Off Voltage	$V_{DS} = 10V$	$I_D = 100mA$	0.15		1.5	V
$V_{DS(SAT)}^*$ Drain – Source Saturation Voltage	$V_{GD} = 0$	$I_D = 8A$			12	V
I_{DSX} Drain – Source Cut-Off Current	$V_{GS} = -10V$	$V_{DS} = 160V$ BUZ900P			10	mA
		$V_{DS} = 200V$ BUZ901P			10	
y_{fs}^* Forward Transfer Admittance	$V_{DS} = 10V$	$I_D = 3A$	0.7		2	S

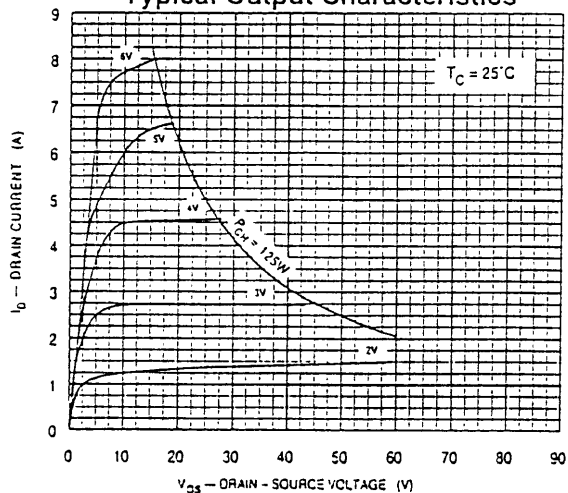
DYNAMIC CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss} Input Capacitance	$V_{DS} = 10V$ $f = 1MHz$		500		pF
C_{oss} Output Capacitance			300		
C_{rss} Reverse Transfer Capacitance			10		
t_{on} Turn-on Time	$V_{DS} = 20V$ $I_D = 5A$		100		ns
t_{off} Turn-off Time			50		

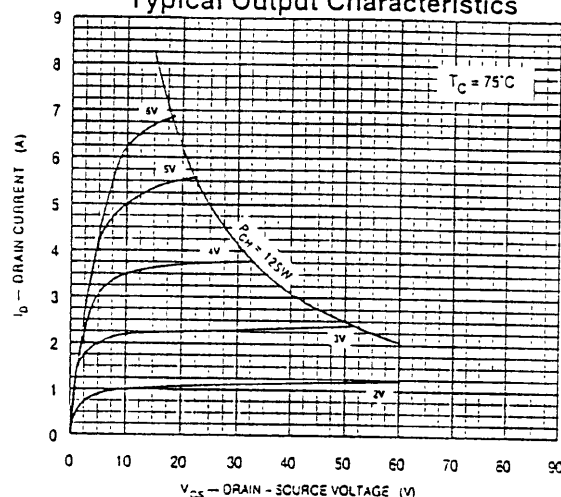
* Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2\%$.



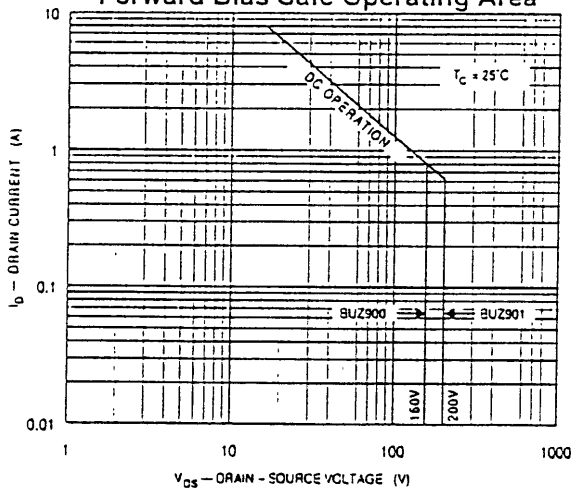
Typical Output Characteristics



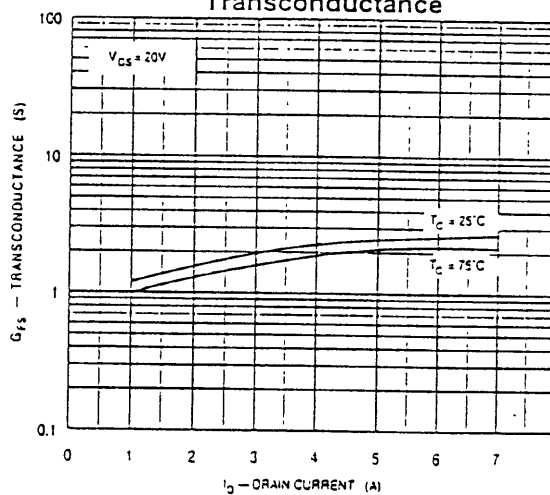
Typical Output Characteristics



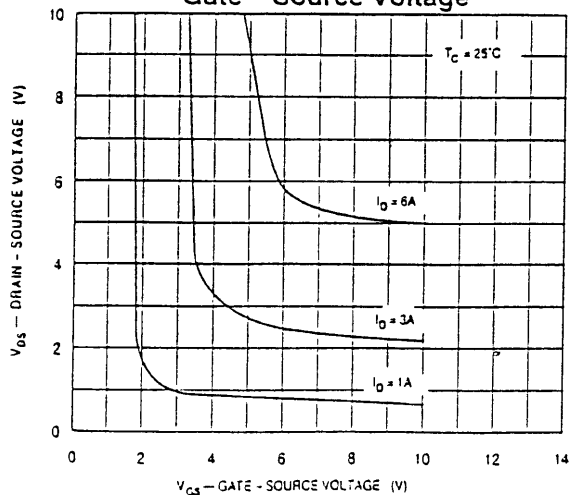
Forward Bias Safe Operating Area



Transconductance



Drain - Source Voltage
vs
Gate - Source Voltage



Typical Transfer Characteristics

